

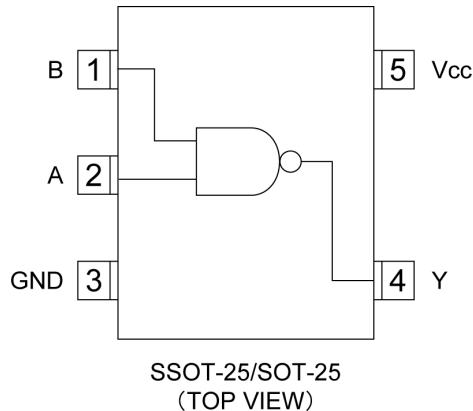
CMOS Logic

- ◆ CMOS 2-Input NAND Gate
- ◆ High Speed Operation : tpd = 2.6ns (TYP.)
- ◆ Operating Voltage Range : 2V ~ 5.5V
- ◆ Low Power Consumption : 1 μ A (MAX.)

■ GENERAL DESCRIPTION

The XC74UL00AA is a 2-input CMOS NAND Gate, manufactured using silicon gate CMOS fabrication. CMOS low power circuit operation makes high speed LS-TTL operation achievable. With a wave forming buffer connected internally, stabilized output can be achieved as the circuit offers high noise immunity. As the XC74UL00AA is integrated into mini molded, SSOT-25 and SOT-25 packages, high density mounting is possible.

■ PIN CONFIGURATION



■ APPLICATIONS

- Palmtops
- Digital equipment

■ FEATURES

- High Speed Operation** : tpd = 2.6ns (TYP.)
Operating Voltage Range : 2V ~ 5.5V
Low Power Consumption: 1 μ A (MAX.)
Ultra Small Package : SSOT-25 and SOT-25

■ FUNCTIONS

INPUT		OUTPUT
A	B	Y
L	L	H
L	H	H
H	L	H
H	H	L

H=High level

L=Low level

■ ABSOLUTE MAXIMUM RATINGS

Ta=-40°C~85°C

PARAMETER	SYMBOL	RATINGS	UNITS
Supply Voltage	Vcc	-0.5~+6.0	V
Input Voltage	Vin	-0.5~+6.0	V
Output Voltage	Vout	-0.5~Vcc+0.5	V
Input Diode Current	Iik	-20	mA
Output Diode Current	lok	± 20	mA
Output Current	Iout	± 25	mA
Vcc,GND Current	Icc, Ignd	± 50	mA
Power Dissipation(Ta=55°C)	Pd	150	mW
Storage Temperature Range	Tstg	-65~+150	°C

* Voltage is all ground standardized.

■ RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	Vcc(V)	CONDITIONS	UNITS
Supply Voltage	Vcc	—	2~5.5	V
Input Voltage	V _{IN}	—	0~5.5	V
Output Voltage	V _{OUT}	—	0~Vcc	V
Operating Temperature Range	T _{opr}	—	-40~+85	°C
Output Current	I _{OH}	3.0	-4	mA
		4.5	-8	
	I _{OL}	3.0	4	
		4.5	8	
Input Rise and Fall Time	t _{r,tf}	3.3	0~100	ns/V
		5.0	0~20	

■ DC ELECTRICAL CHARACTERISTICS

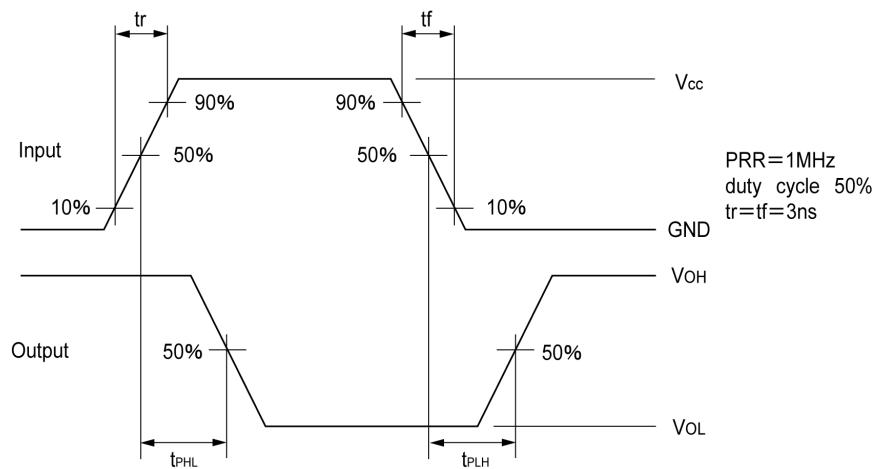
PARAMETER	SYMBOL	CONDITIONS			Ta=25°C			Ta=-40°C~85°C		UNITS
					MIN.	TYP.	MAX.	MIN.	MAX.	
Input Voltage	V _{IH}	2.0			1.5	—	—	1.5	—	V
		3.0			2.1	—	—	2.1	—	
		5.5			3.85	—	—	3.85	—	
	V _{IL}	2.0			—	—	0.5	—	0.5	V
		3.0			—	—	0.9	—	0.9	
		5.5			—	—	1.65	—	1.65	
Output Voltage	V _{OH}	2.0	V _{IN} =V _{IH} or V _{IL}	I _{OH} =-50 μA	1.9	2.0	—	1.9	—	V
		3.0			2.9	3.0	—	2.9	—	
		4.5			4.4	4.5	—	4.4	—	
		3.0		I _{OH} =-4mA	2.58	—	—	2.48	—	
		4.5		I _{OH} =-8mA	3.94	—	—	3.80	—	
	V _{OL}	2.0	V _{IN} =V _{IH}	I _{OL} =50 μA	—	—	0.1	—	0.1	V
		3.0			—	—	0.1	—	0.1	
		4.5			—	—	0.1	—	0.1	
		3.0		I _{OL} =4mA	—	—	0.36	—	0.44	
		4.5		I _{OL} =8mA	—	—	0.36	—	0.44	
Input Current	I _{IN}	0~5.5	V _{IN} =V _{CC} or GND		-0.1	—	0.1	-1.0	1.0	μA
Static Supply Current	I _{CC}	5.5	V _{IN} =V _{CC} or GND, I _{OUT} =0 μA		—	—	1.0	—	10.0	

■ SWITCHING ELECTRICAL CHARACTERISTICS

tr=tf=3ns

PARAMETER	SYMBOL	CONDITIONS			Ta=25°C			Ta=-40°C~85°C		UNITS
					MIN.	TYP.	MAX.	MIN.	MAX.	
Delay Time	t _{PLH}	15pF	3.3		—	3.7	7.9	1.0	9.5	ns
			5.0		—	2.7	5.5	1.0	6.5	
		50pF	3.3		—	5.4	11.4	1.0	13.0	ns
			5.0		—	3.6	7.5	1.0	8.5	
	t _{PHL}	15pF	3.3		—	3.3	7.9	1.0	9.5	ns
			5.0		—	2.5	5.5	1.0	6.5	
		50pF	3.3		—	4.6	11.4	1.0	13.0	ns
			5.0		—	3.5	7.5	1.0	8.5	
Input Capacitance	C _{IN}	—	5.0	V _{IN} =V _{CC} or GND	—	2	10	—	10	pF
Power Dissipation Capacitance	C _{PD}	No Load, f=1MHz			—	9.3	—	—	—	pF

■ WAVEFORM



■ TEST CIRCUIT

